ALPHA & OMEGA SEMICONDUCTOR

AO7417

20V P-Channel MOSFET

General Description

The AO7417 uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge and operation with gate voltages as low as 1.5V, in the small SOT363 footprint. This device is suitable for use in buck convertor.

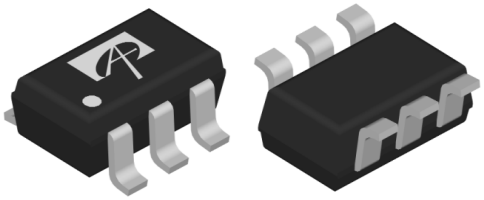
Product Summary

V_{DS}	-20V
I_D (at V_{GS}=-4.5V)	-2A
$R_{DS(ON)}$ (at V_{GS}=-4.5V)	< 80mΩ
$R_{DS(ON)}$ (at V_{GS}=-2.5V)	< 100mΩ
$R_{DS(ON)}$ (at V_{GS}=-1.8V)	< 125mΩ
$R_{DS(ON)}$ (at V_{GS}=-1.5V)	< 150mΩ

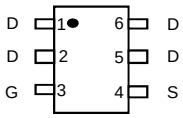
Green Product

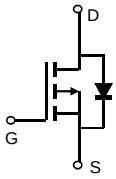
SC-70-6 (SOT-323)

Top View **Bottom View**



Top View





Absolute Maximum Ratings T_A=25℃ unless otherwise noted

Parameter		Symbol	10 Sec	Steady State	Units
Drain-Source Voltage		V_{DS}	-20		V
Gate-Source Voltage		V_{GS}	±8		V
Continuous Drain Current [A]	T_A=25℃	I_D	-2	-1.9	A
	T_A=70℃		-1.7	-1.6	
Pulsed Drain Current [B]		I_{DM}	-20		
Power Dissipation [A]	T_A=25℃	P_D	0.63	0.57	W
	T_A=70℃		0.4	0.36	
Junction and Storage Temperature Range		T_J, T_{STG}	-55 to 150		℃

Thermal Characteristics

Parameter		Symbol	Typ	Max	Units
Maximum Junction-to-Ambient [A]	t ≤ 10s	$R_{\theta JA}$	160	200	℃/W
Maximum Junction-to-Ambient [A]	Steady-State		180	220	℃/W
Maximum Junction-to-Lead [C]	Steady-State	$R_{\theta JL}$	130	160	℃/W

Electrical Characteristics (T_J=25°C unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
STATIC PARAMETERS						
BV_{DSS}	Drain-Source Breakdown Voltage	I_D=-250µA, V_{GS}=0V	-20			V
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS}=-20V,V_{GS}=0V			-1	µA
		T_J=55°C			-5	
I_{GSS}	Gate-Body leakage current	V_{DS}=0V, V_{GS}=±8V			±100	nA
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS}=V_{GS} I_D=-250µA	-0.5	-0.65	-1	V
$I_{D(ON)}$	On state drain current	V_{GS}=-4.5V, V_{DS}=-5V	-20			A
$R_{DS(ON)}$	Static Drain-Source On-Resistance	V_{GS}=-4.5V, I_D=-2A		65	80	mΩ
		T_J=125°C		90	110	
		V_{GS}=-2.5V, I_D=-1.8A		80	100	mΩ
		V_{GS}=-1.8V, I_D=-1.5A		100	125	mΩ
		V_{GS}=-1.5V, I_D=-0.5A		115	150	mΩ
g_{FS}	Forward Transconductance	V_{DS}=-5V, I_D=-2A		10		S
V_{SD}	Diode Forward Voltage	I_S=-1A,V_{GS}=0V		-0.7	-1	V
I_S	Maximum Body-Diode Continuous Current				-1	A
DYNAMIC PARAMETERS						
C_{iss}	Input Capacitance	V_{GS}=0V, V_{DS}=-10V, f=1MHz		560	745	pF
C_{oss}	Output Capacitance			80		pF
C_{rss}	Reverse Transfer Capacitance			70		pF
R_g	Gate resistance	V_{GS}=0V, V_{DS}=0V, f=1MHz		15	23	Ω
SWITCHING PARAMETERS						
Q_g	Total Gate Charge	V_{GS}=-4.5V, V_{DS}=-10V, I_D=-2A		8.5	11	nC
Q_{gs}	Gate Source Charge			1.2		nC
Q_{gd}	Gate Drain Charge			2.1		nC
$t_{D(on)}$	Turn-On DelayTime	V_{GS}=-4.5V, V_{DS}=-10V, R_L=5Ω, R_{GEN}=6Ω		7.2		ns
t_r	Turn-On Rise Time			36		ns
$t_{D(off)}$	Turn-Off DelayTime			53		ns
t_f	Turn-Off Fall Time			56		ns
t_{rr}	Body Diode Reverse Recovery Time	I_F=-2A, dI/dt=100A/µs		37	49	ns
Q_{rr}	Body Diode Reverse Recovery Charge	I_F=-2A, dI/dt=100A/µs		27		nC

A: The value of $R_{\theta JA}$ is measured with the device mounted on 1in^2 FR-4 board with 2oz. Copper, in a still air environment with T_A=25° C. The value in any a given application depends on the user's specific board design. The current rating is based on the t ≤ 10s thermal resistance rating.
B: Repetitive rating, pulse width limited by junction temperature.
C. The $R_{\theta JA}$ is the sum of the thermal impedence from junction to lead $R_{\theta JL}$ and lead to ambient.
D. The static characteristics in Figures 1 to 6 are obtained using 300 µs pulse width, duty cycle 0.5% max.
E. These tests are performed with the device mounted on 1 in^2 FR-4 board with 2oz. Copper, in a still air environment with T_A=25° C. The SOA curve provides a single pulse rating.

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

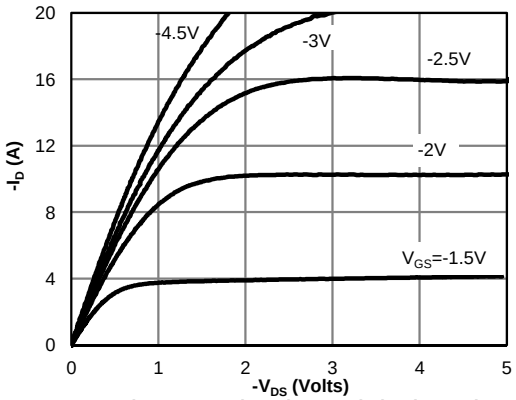


Fig 1: On-Region Characteristics (Note E)

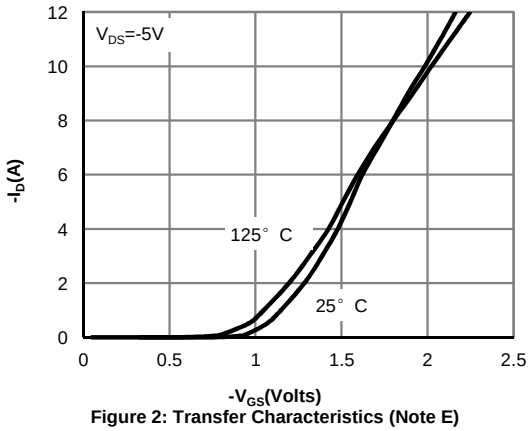


Figure 2: Transfer Characteristics (Note E)

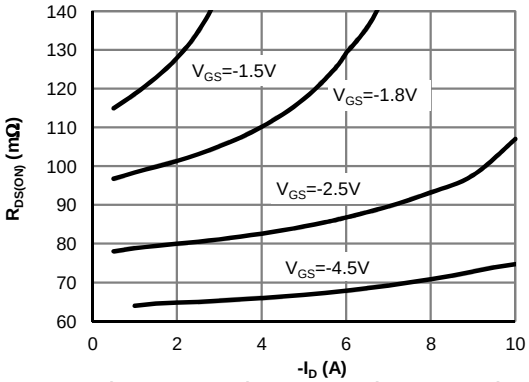


Figure 3: On-Resistance vs. Drain Current and Gate Voltage (Note E)

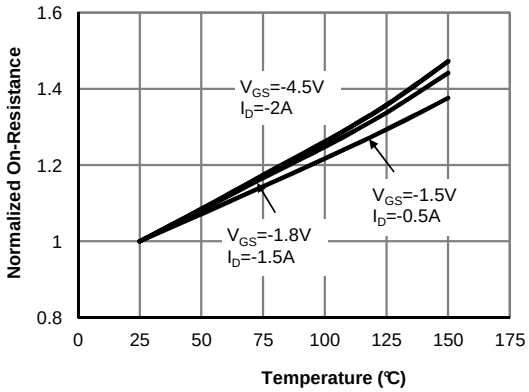


Figure 4: On-Resistance vs. Junction Temperature (Note E)

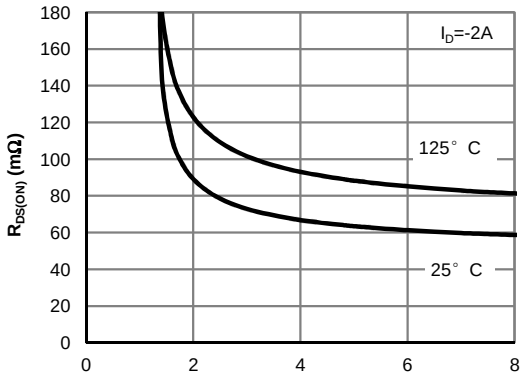


Figure 5: On-Resistance vs. Gate-Source Voltage (Note E)

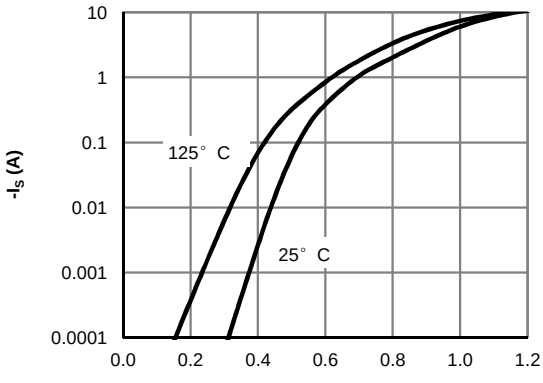


Figure 6: Body-Diode Characteristics (Note E)

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

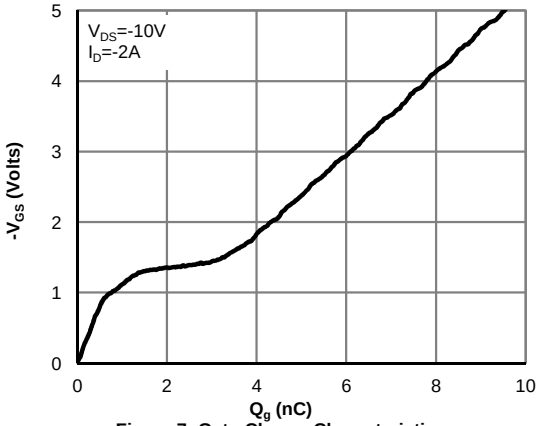


Figure 7: Gate-Charge Characteristics

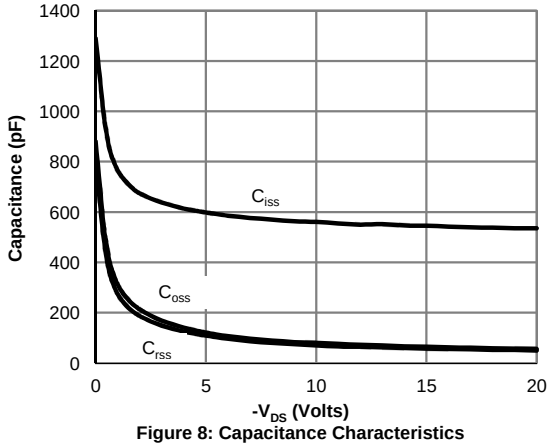


Figure 8: Capacitance Characteristics

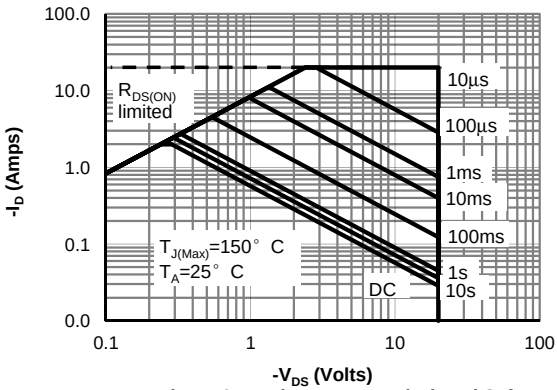


Figure 9: Maximum Forward Biased Safe Operating Area (Note F)

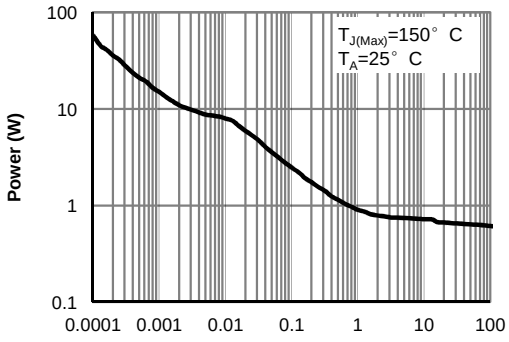


Figure 10: Single Pulse Power Rating Junction-to-Ambient (Note F)

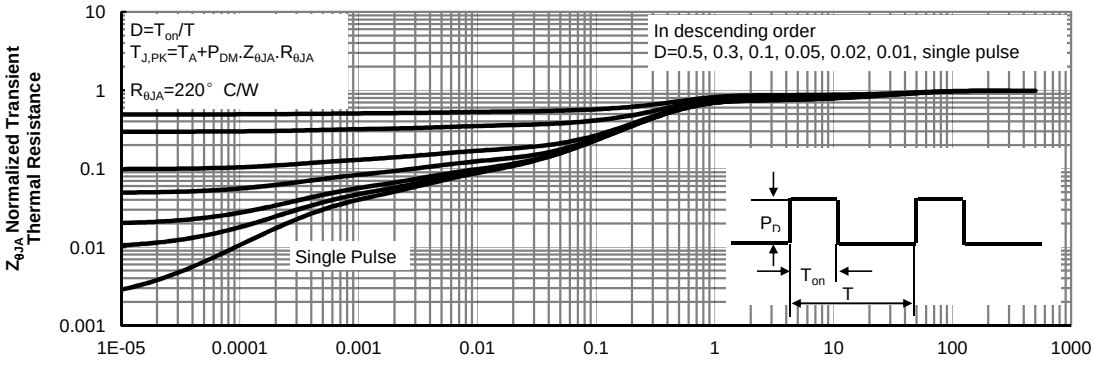


Figure 11: Normalized Maximum Transient Thermal Impedance (Note F)